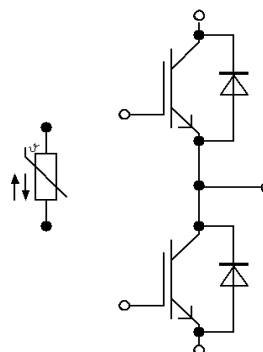
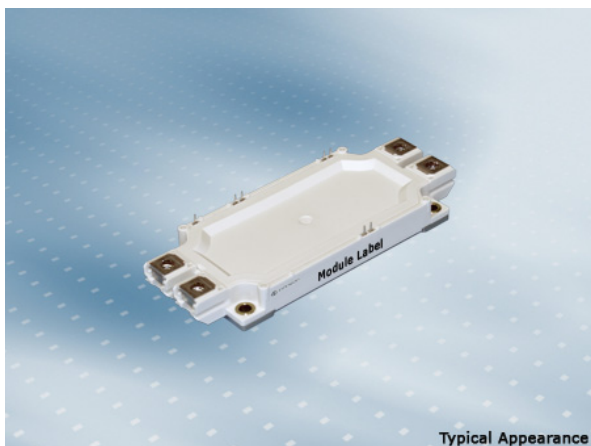


EconoDUAL™3 Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled HE Diode und PressFIT / NTC / TIM

EconoDUAL™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled HE diode and PressFIT / NTC / TIM



$V_{CES} = 1200V$

$I_{C\ nom} = 225A / I_{CRM} = 450A$

Typische Anwendungen

- Motorantriebe
- Servoumrichter
- USV-Systeme
- Windgeneratoren

Elektrische Eigenschaften

- Niedriges V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Mechanische Eigenschaften

- Standardgehäuse
- Thermisches Interface Material bereits aufgetragen

Typical Applications

- Motor drives
- Servo drives
- UPS systems
- Wind turbines

Electrical Features

- Low V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Mechanical Features

- Standard housing
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, Wechselrichter / IGBT, Inverter**Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 70^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$	225	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	450	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 225\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 225\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 225\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,85 2,10 2,15	2,15	V V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 7,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	1,55		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	3,3		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	13,0		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,705		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		3,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0,16 0,17 0,18		μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,04 0,04 0,04		μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0,38 0,47 0,50		μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,07 0,09 0,10		μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}, L_S = 80\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 5750\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	6,80 12,5 15,0		mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 225\text{ A}, V_{CE} = 600\text{ V}, L_S = 80\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3400\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	17,0 26,5 29,5		mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	900		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}		0,175	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

Diode, Wechselrichter / Diode, Inverter**Höchstzulässige Werte / Maximum Rated Values**

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	225	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	450	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	10000 8100	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 225\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 225\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 225\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,65 1,65 1,65	2,10	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 225\text{ A}, -di_F/dt = 5750\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	300 320 340		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 225\text{ A}, -di_F/dt = 5750\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	22,5 43,0 49,5		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 225\text{ A}, -di_F/dt = 5750\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	12,0 22,0 25,0		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode valid with IFX pre-applied thermal interface material		R_{thJH}		0,197	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
Abweichung von R100 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\text{ }\Omega$	$\Delta R/R$	-5		5	%
Verlustleistung Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

Angaben gemäß gültiger Application Note.

Specification according to the valid application note.

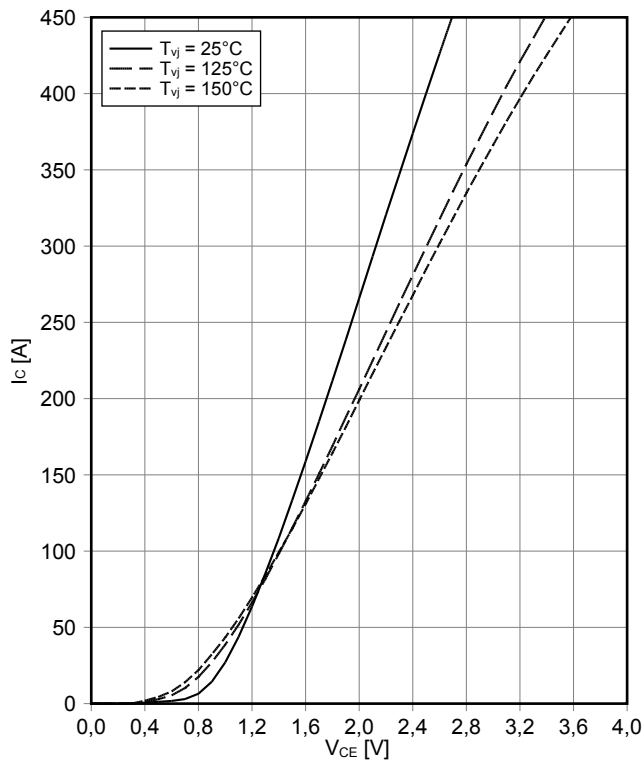
Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min	V _{ISOL}	2,5		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		14,5 13,0		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		12,5 10,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 200		
			min.	typ.	max.
Modulstreuinduktivität Stray inductance module		L _{sCE}		20	nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _H = 25°C, pro Schalter / per switch	R _{CC'+EE'}		1,30	mΩ
Lagertemperatur Storage temperature		T _{stg}	-40		125 °C
Höchstzulässige Bodenplattenbetriebstemperatur Maximum baseplate operation temperature		T _{BPmax}			125 °C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00		6,00 Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note	M	3,0	-	6,0 Nm
Gewicht Weight		G		345	g

Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
 Storage and shipment of modules with TIM => see AN2012-07

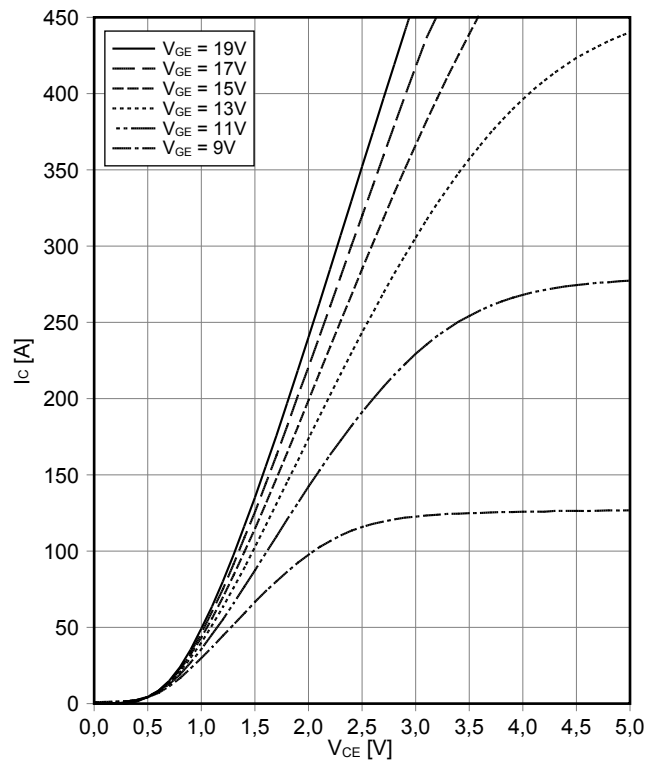
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



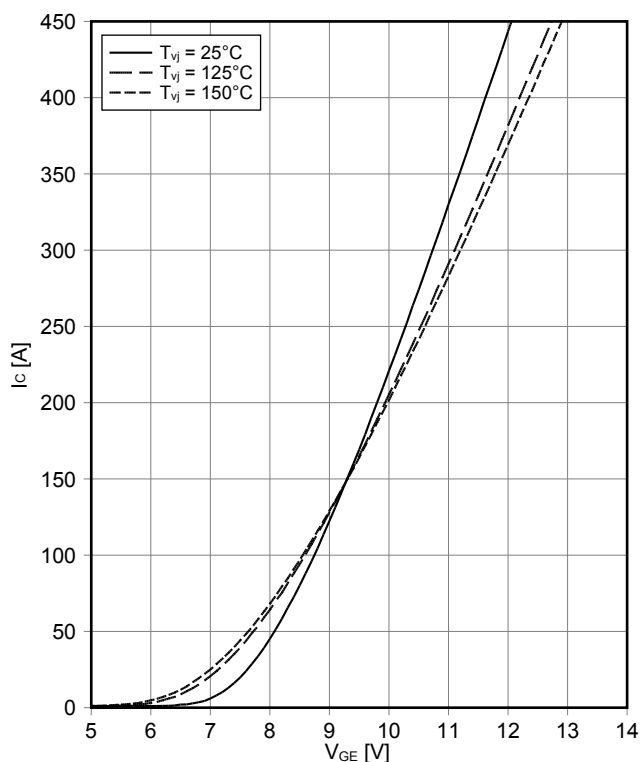
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



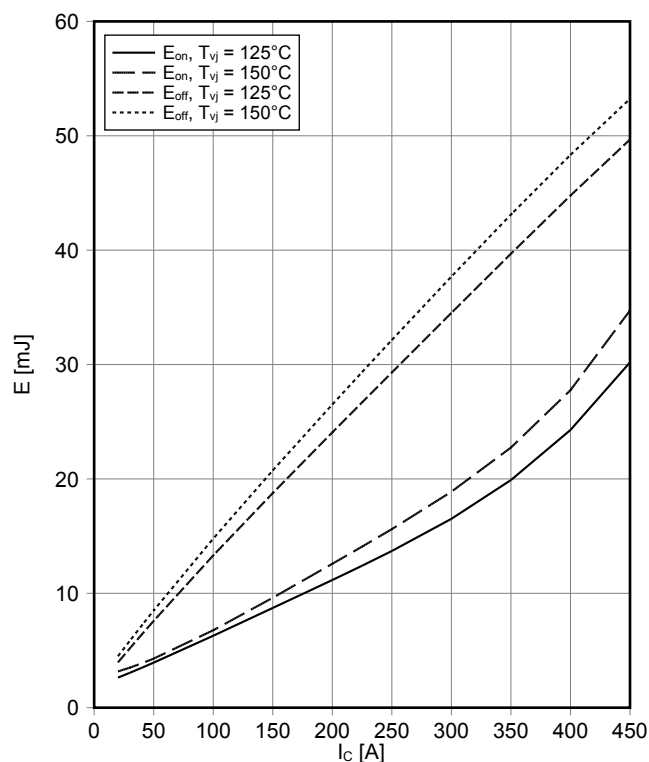
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20 \text{ V}$



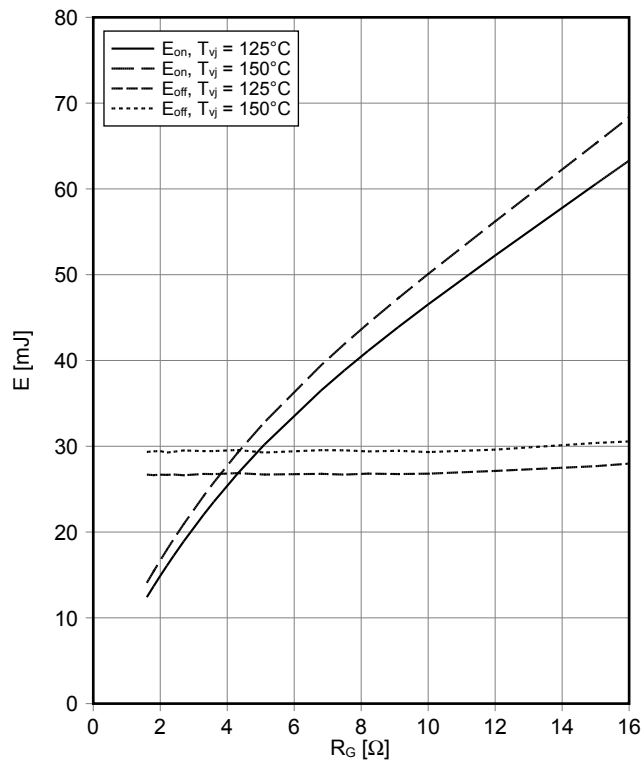
Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 1.6 \Omega$, $R_{Goff} = 1.6 \Omega$, $V_{CE} = 600 \text{ V}$



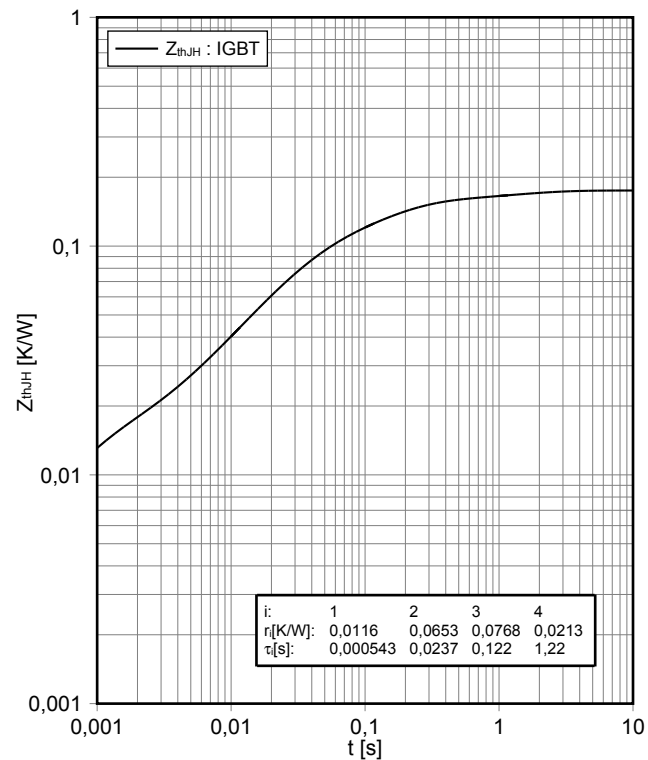
Schaltverluste IGBT, Wechselrichter (typisch) switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 225 \text{ A}$, $V_{CE} = 600 \text{ V}$



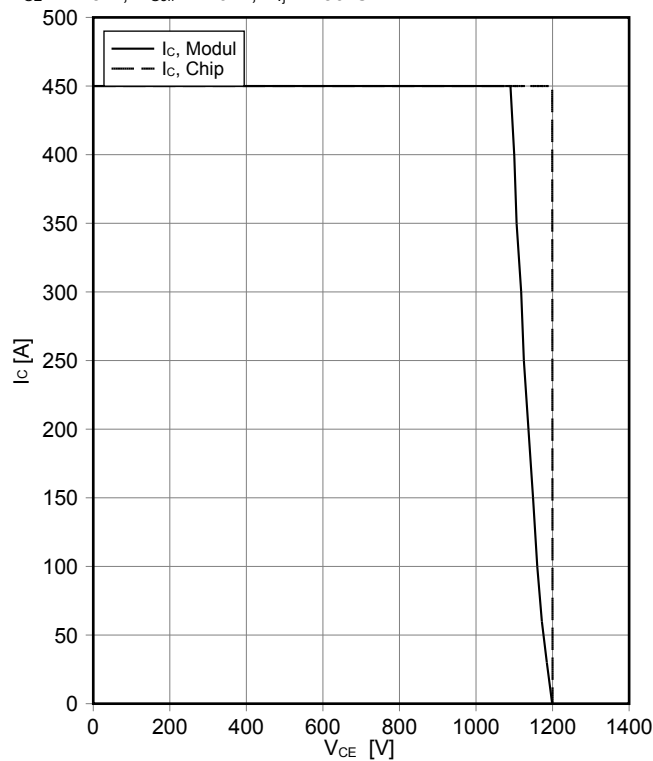
Transienter Wärmewiderstand IGBT, Wechselrichter transient thermal impedance IGBT, Inverter

$Z_{thJH} = f(t)$



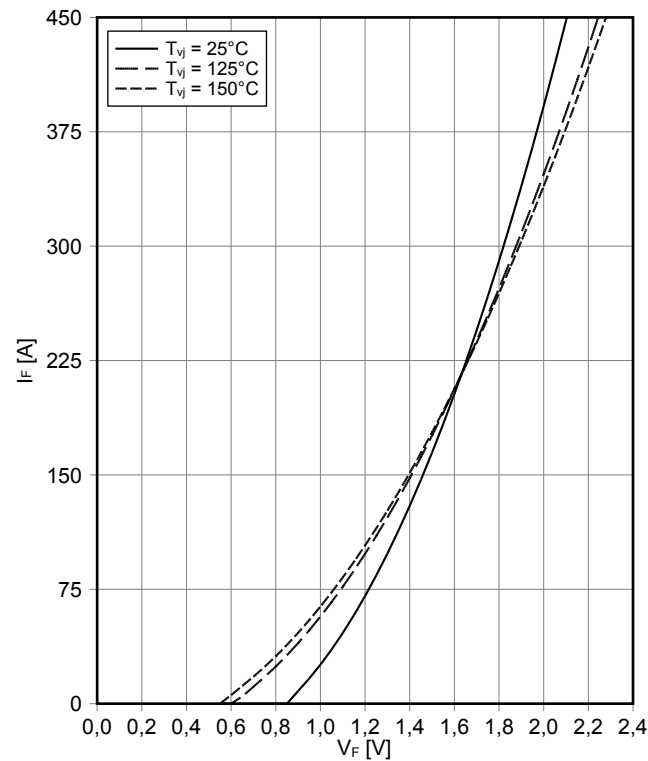
Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter (RBSOA) reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 1.6 \Omega$, $T_{vj} = 150^\circ\text{C}$



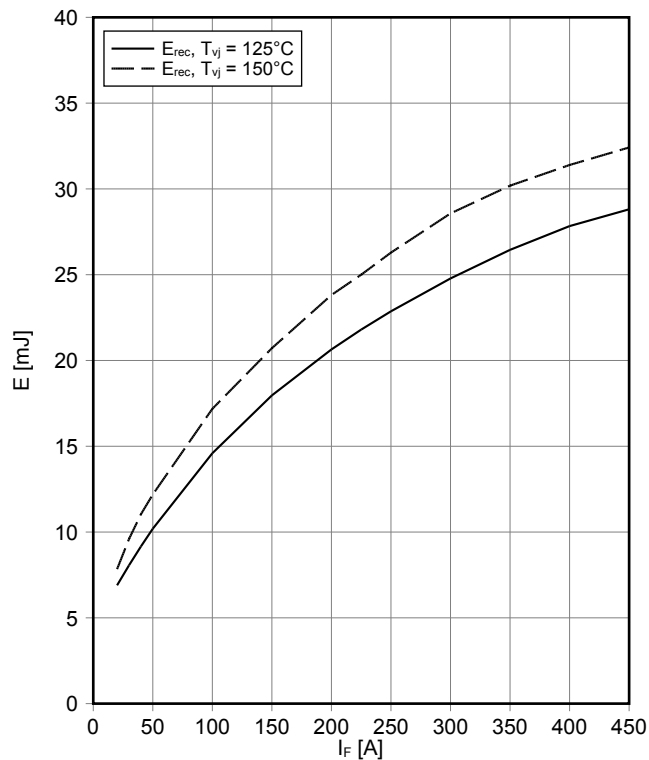
Durchlasskennlinie der Diode, Wechselrichter (typisch) forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



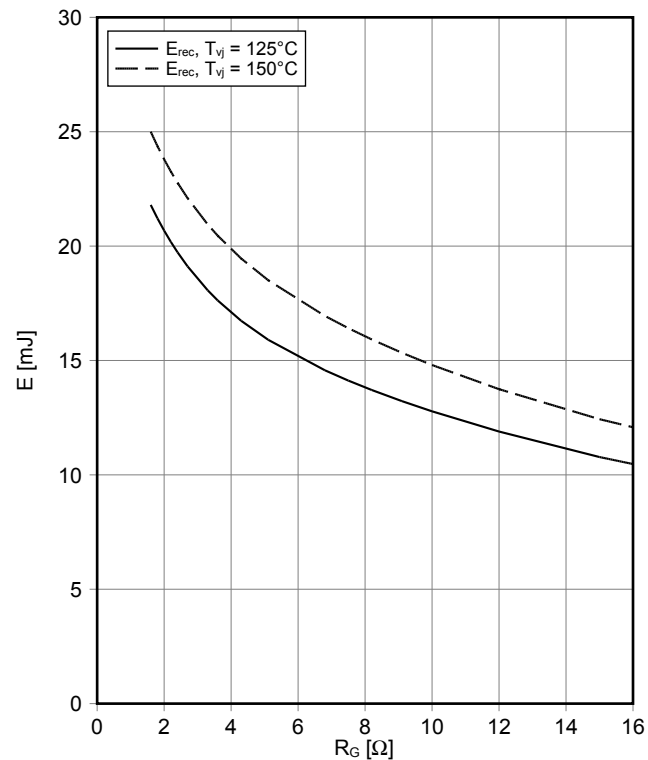
Schaltverluste Diode, Wechselrichter (typisch) switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.6 \Omega$, $V_{CE} = 600 V$



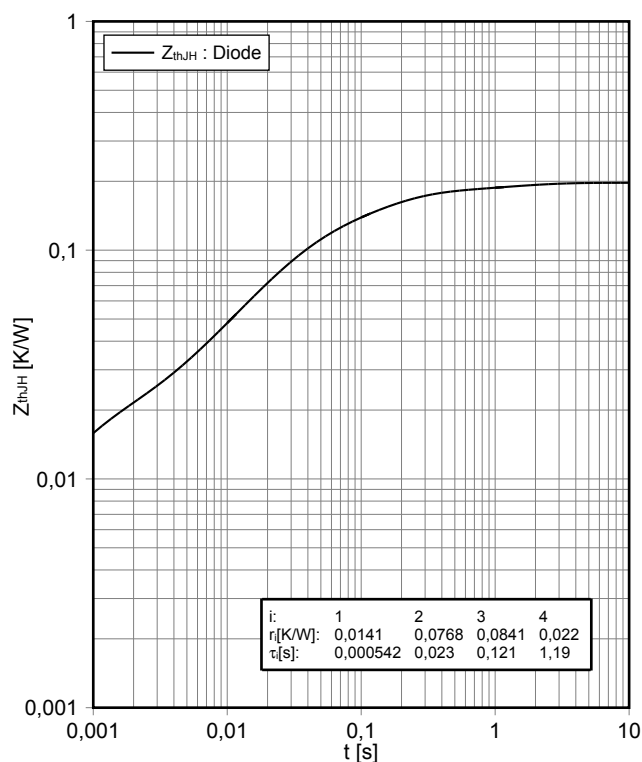
Schaltverluste Diode, Wechselrichter (typisch) switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 225 A$, $V_{CE} = 600 V$



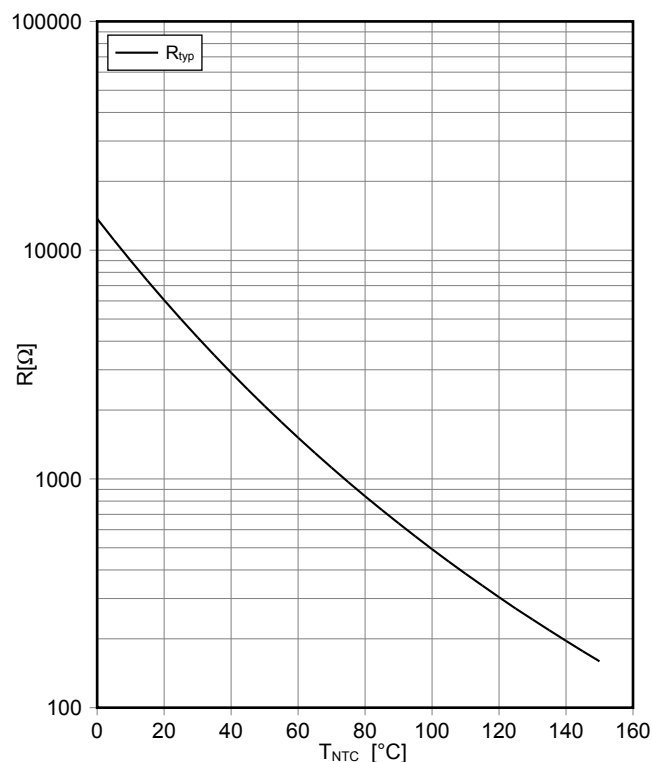
Transienter Wärmewiderstand Diode, Wechselrichter transient thermal impedance Diode, Inverter

$Z_{thJH} = f(t)$



NTC-Widerstand-Temperaturkennlinie (typisch) NTC-Thermistor-temperature characteristic (typical)

$R = f(T)$



Technical drawing of the Infineon EconoDUAL™ module showing top, side, and front views with dimensions in mm.

Top View Dimensions:

- Overall width: 152±0.5
- Overall height: 62±0.2
- Internal width: 94.5±0.2
- Internal height: 57.5±0.2
- Mounting hole diameter: $\phi 5 \pm 0.2$
- Mounting hole position: 116-0.6
- Mounting hole offset: 6±0.1
- Internal width (excluding mounting holes): 100.6±0.3
- Internal height (excluding mounting holes): 37.2±0.5
- Internal width (excluding mounting holes and internal features): 79.2±0.3
- Internal height (excluding mounting holes and internal features): 20.7±0.2
- Internal width (excluding mounting holes and internal features): 94.5±0.2
- Internal height (excluding mounting holes and internal features): 38.6±0.2
- Internal width (excluding mounting holes and internal features): 110±0.2
- Internal height (excluding mounting holes and internal features): 122.5±0.5
- Internal width (excluding mounting holes and internal features): 137±0.6
- Internal height (excluding mounting holes and internal features): 152±0.5

Side View Dimensions:

- Overall height: 120.5
- Mounting hole diameter: $\phi 5 \pm 0.2$
- Mounting hole position: 116-0.6
- Mounting hole offset: 6±0.1
- Internal width: 100.6±0.3
- Internal height: 37.2±0.5
- Internal width (excluding mounting holes): 79.2±0.3
- Internal height (excluding mounting holes): 20.7±0.2
- Internal width (excluding mounting holes and internal features): 94.5±0.2
- Internal height (excluding mounting holes and internal features): 38.6±0.2
- Internal width (excluding mounting holes and internal features): 110±0.2
- Internal height (excluding mounting holes and internal features): 122.5±0.5
- Internal width (excluding mounting holes and internal features): 137±0.6
- Internal height (excluding mounting holes and internal features): 152±0.5

Front View Dimensions:

- Overall width: 152±0.5
- Overall height: 62±0.2
- Internal width: 94.5±0.2
- Internal height: 57.5±0.2
- Mounting hole diameter: $\phi 5 \pm 0.2$
- Mounting hole position: 116-0.6
- Mounting hole offset: 6±0.1
- Internal width (excluding mounting holes): 100.6±0.3
- Internal height (excluding mounting holes): 37.2±0.5
- Internal width (excluding mounting holes): 79.2±0.3
- Internal height (excluding mounting holes): 20.7±0.2
- Internal width (excluding mounting holes and internal features): 94.5±0.2
- Internal height (excluding mounting holes and internal features): 38.6±0.2
- Internal width (excluding mounting holes and internal features): 110±0.2
- Internal height (excluding mounting holes and internal features): 122.5±0.5
- Internal width (excluding mounting holes and internal features): 137±0.6
- Internal height (excluding mounting holes and internal features): 152±0.5

Leiterplatten-Lochbild / PCB drillhole pattern

1) $\phi 1.00 \pm 0.02$ Durchmesser des metallierten Loches
 $\phi 1.00 \pm 0.02$ Diameter of finished plated-through hole
 $\phi 1.15$ Bohrungsdurchmesser des Loches
 $\phi 1.15$ Diameter of drilled hole

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